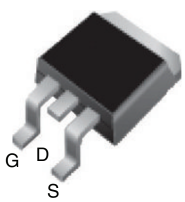
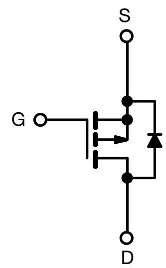
Power MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	-200	
$R_{DS(on)}$ (Ω)	V_{GS} = -10 V	0.80
Q_g max. (nC)	29	
Q_{gs} (nC)	5.4	
Q_{gd} (nC)	15	
Configuration	Single	

D2PAK (TO-263)





P-Channel MOSFET

FEATURES

- Surface mount
- Available in tape and reel
- Dynamic dV/dt rating
- Repetitive avalanche rated
- P-channel
- Fast switching
- Ease of paralleling
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

RoHS* Available
HALOGEN FREE Available

Note

* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non-RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details.

DESCRIPTION

Third generation power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The D2PAK (TO-263) is a surface mount power package capable of accommodating die size up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D2PAK (TO-263) is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0 W in a typical surface mount application.

ORDERING INFORMATION		
Package	D2PAK (TO-263)	D2PAK (TO-263)
Lead (Pb)-free and Halogen-free	SiHF9630S-GE3	SiHF9630STRL-GE3 [a]
Lead (Pb)-free	IRF9630SPbF	IRF9630STRLPbF [a]
	SiHF9630S-E3	SiHF9630STL-E3 [a]

Note

a. See device orientation.

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)					
PARAMETER			**SYMBOL**	**LIMIT**	**UNIT**
Drain-Source Voltage			V_{DS}	-200	V
Gate-Source Voltage			V_{GS}	± 20	
Continuous Drain Current	V_{GS} at -10 V	T_C = 25 °C	I_D	-6.5	A
		T_C = 100 °C		-4.0	
Pulsed Drain Current [a]			I_{DM}	-26	
Linear Derating Factor				0.59	W/°C
Linear Derating Factor (PCB mount) [e]				0.025	
Single Pulse Avalanche Energy [b]			E_{AS}	500	mJ
Avalanche Current [a]			I_{AR}	-6.4	A
Repetitive Avalanche Energy [a]			E_{AR}	7.4	mJ
Maximum Power Dissipation	T_C = 25 °C		P_D	74	W
Maximum Power Dissipation (PCB mount) [e]	T_A = 25 °C			3.0	
Peak Diode Recovery dV/dt [c]			dV/dt	-5.0	V/ns
Operating Junction and Storage Temperature Range			T_J, T_{stg}	-55 to +150	°C
Soldering Recommendations (Peak temperature) [d]	for 10 s			300	

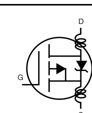
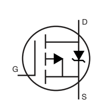
Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
b. V_{DD} = -50 V, starting T_J = 25 °C, L = 17 mH, R_g = 25 Ω, I_{AS} = -6.5 A (see fig. 12).
c. $I_{SD} \leq$ -6.5 A, dI/dt ≤ 120 A/μs, $V_{DD} \leq V_{DS}$, $T_J \leq$ 150 °C.
d. 1.6 mm from case.
e. When mounted on 1" square PCB (FR-4 or G-10 material).

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	62	°C/W
Maximum Junction-to-Ambient (PCB mount) [a]	R_{thJA}	-	40	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	1.7	

Note

a. When mounted on 1" square PCB (FR-4 or G-10 material).

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0, I_D = -250 μA	-200	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C, I_D = -1 mA	-	-0.24	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = -250 μA	-2.0	-	-4.0	V
Gate-Source Leakage	I_{GSS}	V_{GS} = ± 20 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -200 V, V_{GS} = 0 V	-	-	- 100	μA
		V_{DS} = -160 V, V_{GS} = 0 V, T_J = 125 °C	-	-	-500	
Drain-Source On-State Resistance	$R_{DS(on)}$	V_{GS} = -10 V; I_D = -3.9 A [b]	-	-	0.80	Ω
Forward Transconductance	g_{fs}	V_{DS} = -50 V, I_D = -3.9 A [b]	2.8	-	-	S
Dynamic						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = -25 V, f = 1.0 MHz, see fig. 5	-	700	-	pF
Output Capacitance	C_{oss}		-	200	-	
Reverse Transfer Capacitance	C_{rss}		-	40	-	
Total Gate Charge	Q_g	V_{GS} = -10 V; I_D = -6.5 A, V_{DS} = -160 V, see fig. 6 and 13 [b]	-	-	29	nC
Gate-Source Charge	Q_{gs}		-	-	5.4	
Gate-Drain Charge	Q_{gd}		-	-	15	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = -100 V, I_D = -6.5 A, R_g = 12 Ω, R_D = 15 Ω, see fig. 10 [b]	-	12	-	ns
Rise Time	t_r		-	27	-	
Turn-Off Delay Time	$t_{d(off)}$		-	28	-	
Fall Time	t_f		-	24	-	
Internal Drain Inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact 	-	4.5	-	nH
Internal Source Inductance	L_S		-	7.5	-	
Gate Input Resistance	R_g	f = 1 MHz, open drain	0.6	-	3.7	Ω
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	-6.5	A
Pulsed Diode Forward Current [a]	I_{SM}		-	-	-26	
Body Diode Voltage	V_{SD}	T_J = 25 °C, I_S = -6.5 A, V_{GS} = 0 V [b]	-	-	-6.5	V
Body Diode Reverse Recovery Time	t_{rr}	T_J = 25 °C, I_F = -6.5 A, dI/dt = 100 A/μs [b]	-	200	300	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	1.9	2.9	μC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)				

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).

b. Pulse width ≤ 300 μs; duty cycle ≤ 2 %.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

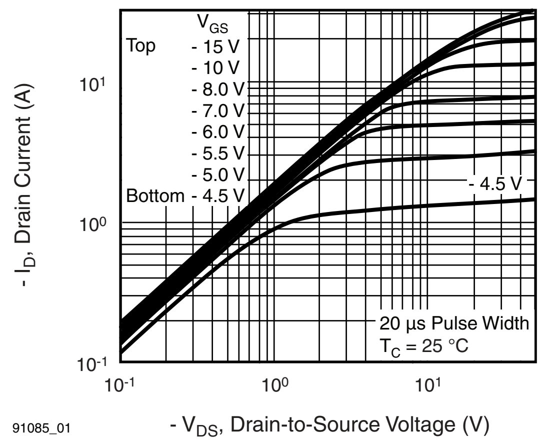


Fig. 1 - Typical Output Characteristics, T_C = 25 °C

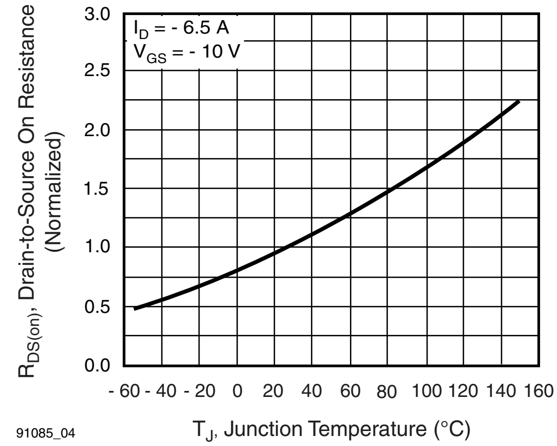


Fig. 4 - Normalized On-Resistance vs. Temperature

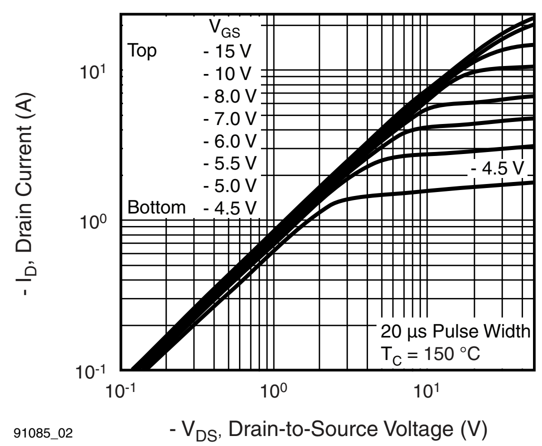


Fig. 2 - Typical Output Characteristics, T_C = 150 °C

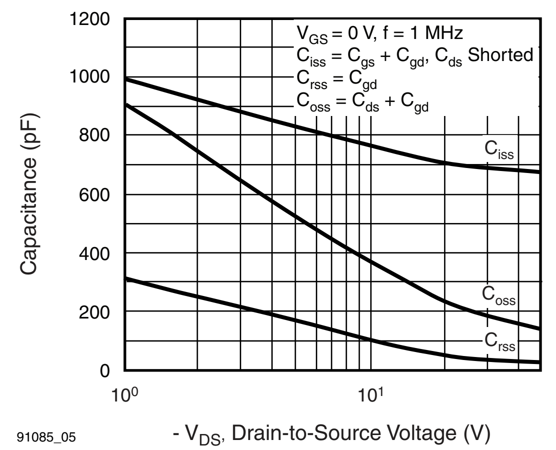


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

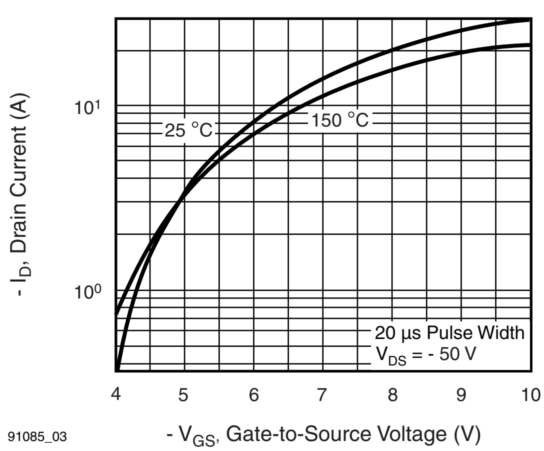


Fig. 3 - Typical Transfer Characteristics

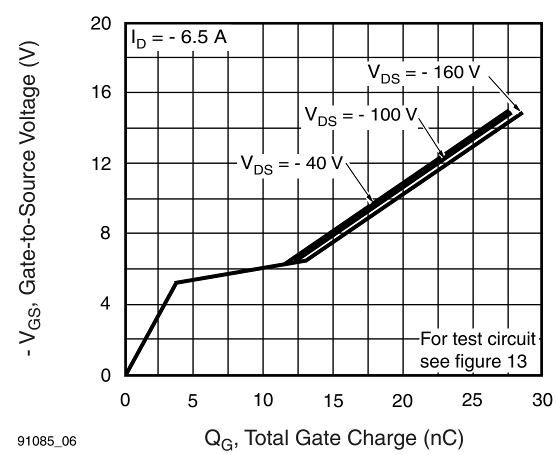


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

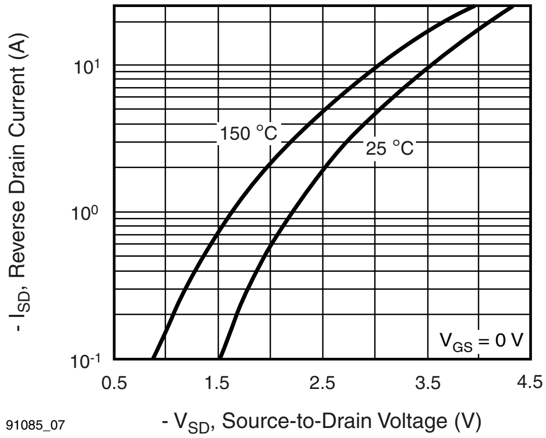


Fig. 7 - Typical Source-Drain Diode Forward Voltage

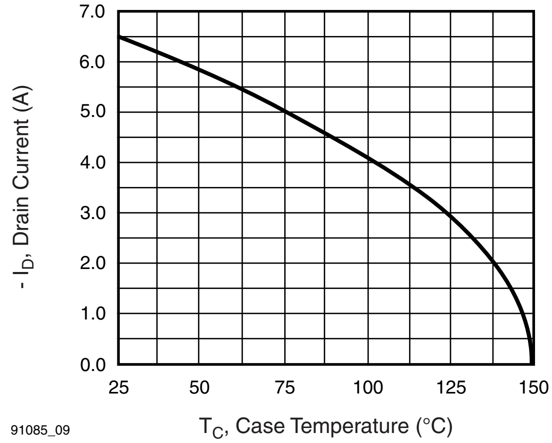


Fig. 9 - Maximum Drain Current vs. Case Temperature

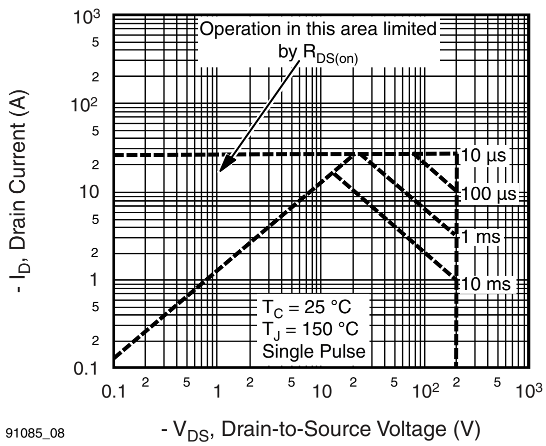


Fig. 8 - Maximum Safe Operating Area

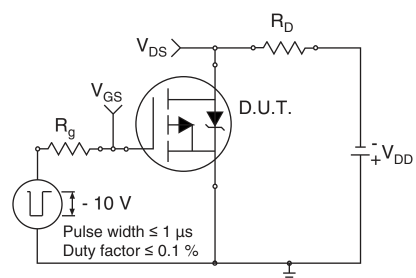


Fig. 10a - Switching Time Test Circuit

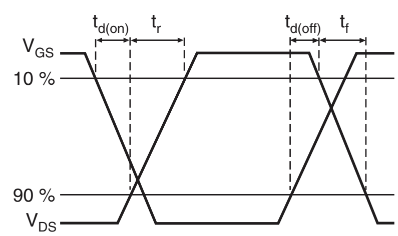


Fig. 10b - Switching Time Waveforms

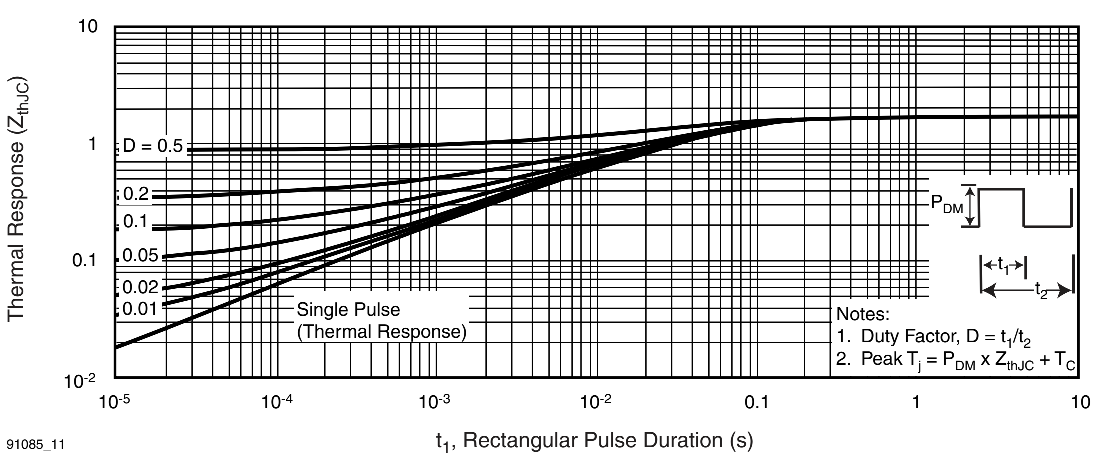


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

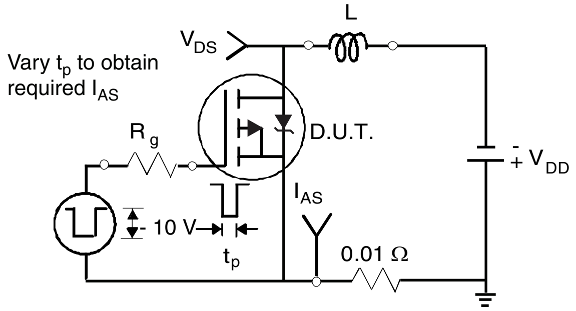


Fig. 12a - Unclamped Inductive Test Circuit

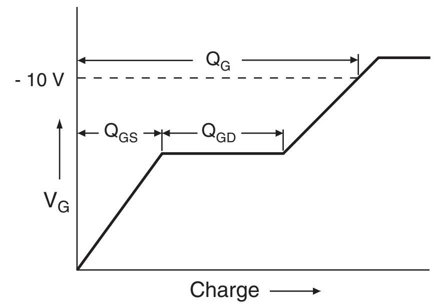


Fig. 13a - Basic Gate Charge Waveform

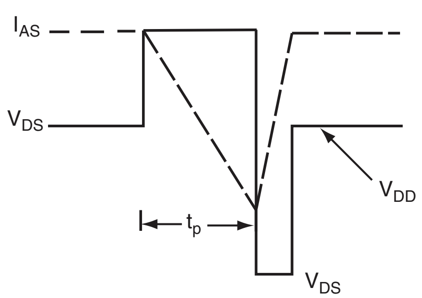


Fig. 12b - Unclamped Inductive Waveforms

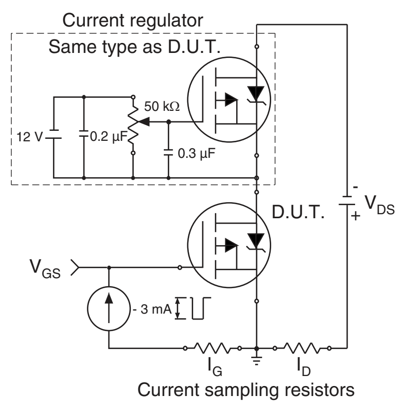


Fig. 13b - Gate Charge Test Circuit

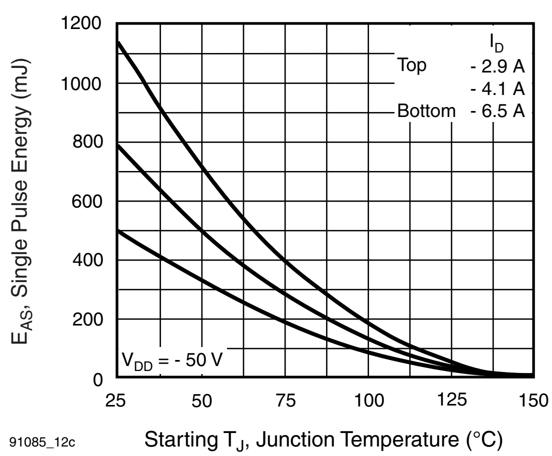
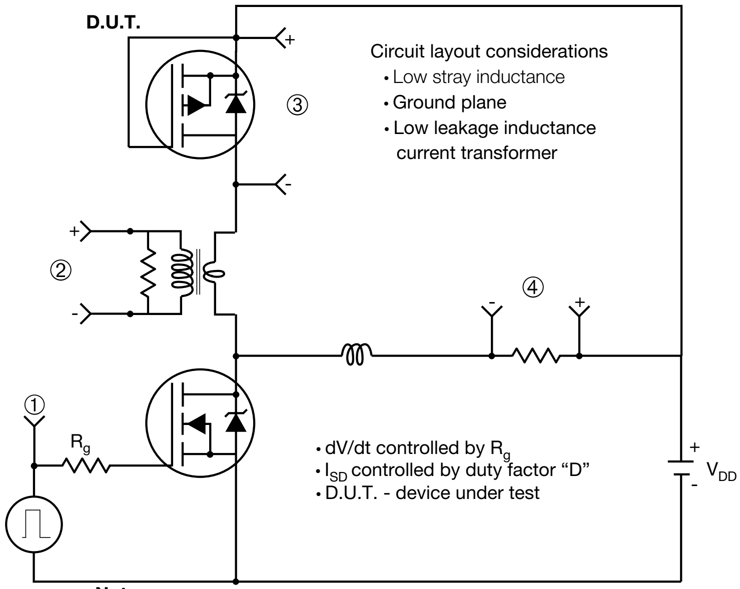


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

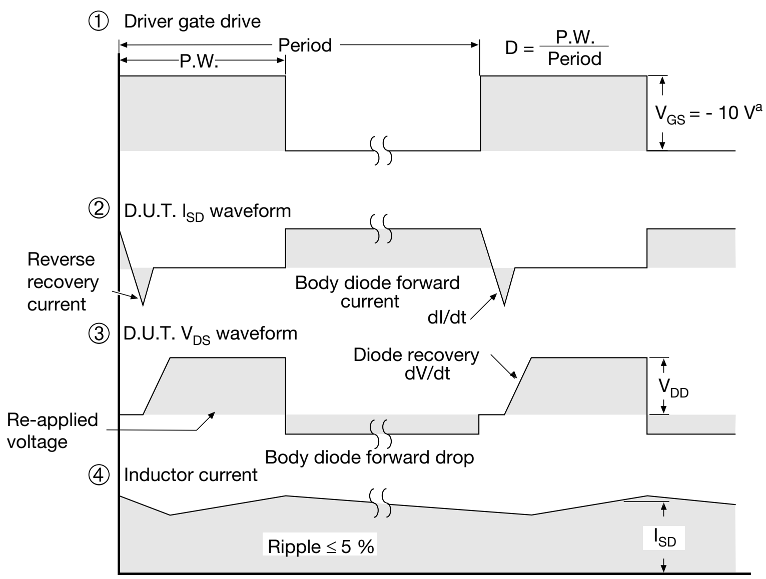
For technical questions, contact: hvm@vishay.com

Peak Diode Recovery dV/dt Test Circuit



Note

- Compliment N-Channel of D.U.T. for driver



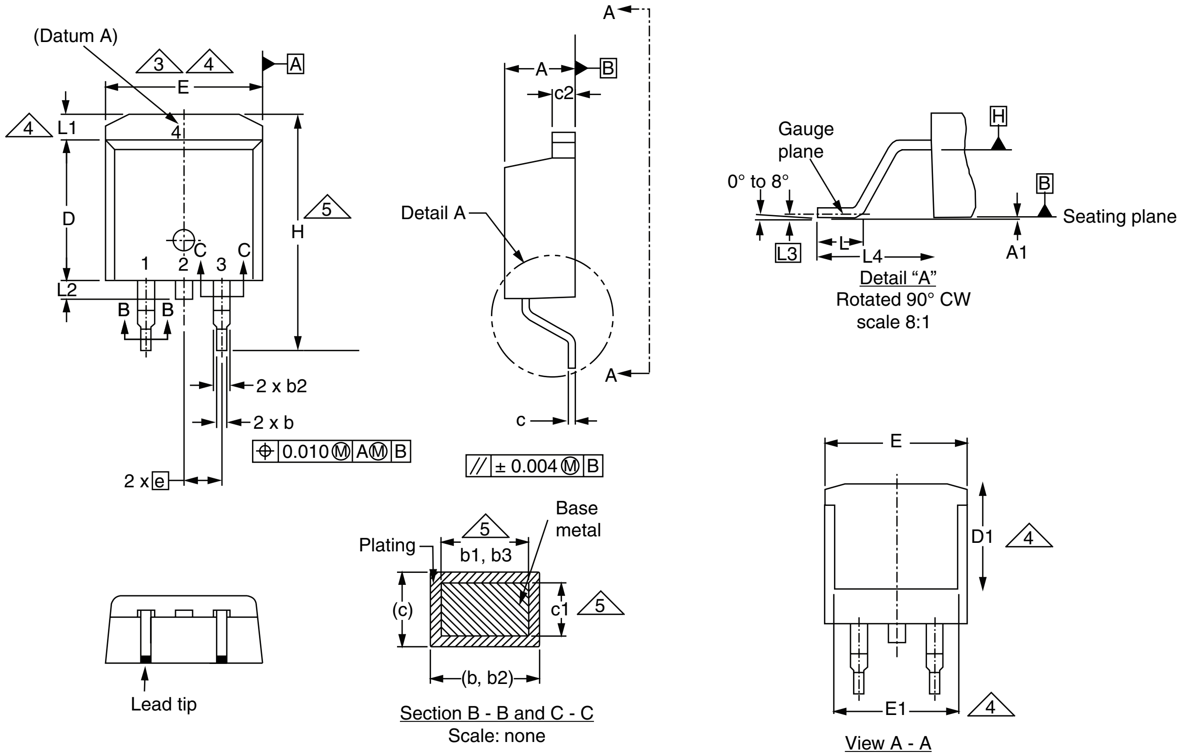
Note

a. V_{GS} = - 5 V for logic level and - 3 V drive devices

Fig. 14 - For P-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?91085.

TO-263AB (HIGH VOLTAGE)



	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	0.00	0.25	0.000	0.010
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
c	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065
D	8.38	9.65	0.330	0.380

	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.65	-	0.066
L2	-	1.78	-	0.070
L3	0.25 BSC		0.010 BSC	
L4	4.78	5.28	0.188	0.208

ECN: S-82110-Rev. A, 15-Sep-08
DWG: 5970

Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimensions are shown in millimeters (inches).
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body at datum A.
4. Thermal PAD contour optional within dimension E, L1, D1 and E1.
5. Dimension b1 and c1 apply to base metal only.
6. Datum A and B to be determined at datum plane H.
7. Outline conforms to JEDEC outline to TO-263AB.

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